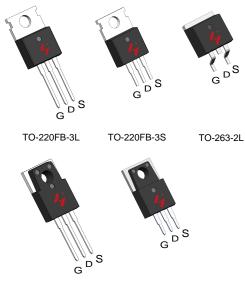


N-Channel Enhancement Mode MOSFET

Features

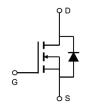
- 150V/120A $R_{DS(ON)} = 12 \text{ m}\Omega \text{ (typ.) } @ V_{GS} = 10V$
- 100% avalanche tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

Pin Description



Applications

- Switching application
- Power Management for Inverter Systems.



TO-3PM-3S

N-Channel MOSFET

Ordering and Marking Information







Package Code

P : TO-220FB-3L M : TO-220FB-3S B: TO-263-2L PS: TO-3PS-3L

TO-3PS-3L

PM: TO-3PM-3S

Date Code Assembly Material
YYXXX WW G: Lead Free Device

Note: HUAYI lead -free products contain molding compounds/die attach materials and 100% matte tin plate Termination finish; which are fully compliant with RoHS. HUAYI lead -free products meet or exceed the lead-Free requirements of IPC/JEDEC J-STD-020 for MSL classification at lead-free peak reflow temperature. HUAYI defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HUAYI reserves the right to make changes, corrections, enhancements, modifications, and improvements to this pr-oduct and/or to this document at any time without notice.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit					
Common	Common Ratings (T _c =25°C Unless Otherwise Noted)							
V _{DSS}	Drain-Source Voltage		150	V				
V _{GSS}	Gate-Source Voltage		±25	\neg				
TJ	Maximum Junction Temperature		175	°C				
T _{STG}	Storage Temperature Range		-55 to 175	°C				
Is	Diode Continuous Forward Current	T _C =25°C	120	А				
Mounted	Mounted on Large Heat Sink							
I _{DM}	Pulsed Drain Current *	T _C =25°C	480**	А				
	Continuous Drain Current	T _C =25°C	120					
l _D	Continuous Drain Current	T _C =100°C	84	_ A				
В	Maximum Dawar Discipation	T _C =25°C	300	W				
P _D	Maximum Power Dissipation	T _C =100°C	150	¬ ~				
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.5	°C ///					
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	- °C/W					
Avalanch	e Ratings							
E _{AS}	Avalanche Energy, Single Pulsed	L=0.5mH	1025***	mJ				

Note: * Repetitive rating; pulse width limited by junction temperature

Electrical Characteristics (T_c = 25°C Unless Otherwise Noted)

Cymhol	Doromotor	Test Conditions	H	HY3215		
Symbol	Parameter	rest Conditions	Min.	Тур.	Max.	Unit
Static Cha	racteristics		•			
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	150	-	-	V
	Zero Gate Voltage Drain Current	V _{DS} =150V, V _{GS} =0V	-	-	1	۸
I _{DSS}	Zero Gate Voltage Drain Current	T _J =85°C	-	-	10	μА
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{DS}=250\mu A$	3.0	4.0	5.0	V
I _{GSS}	Gate Leakage Current	V_{GS} =±25V, V_{DS} =0V	-	-	±100	nA
R _{DS(ON)} *	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =60A	-	12	15	mΩ
Diode Cha	Diode Characteristics					
V _{SD} *	Diode Forward Voltage	I _{SD} =60A, V _{GS} =0V	-	0.8	1	V
t _{rr}	Reverse Recovery Time	I _60A dl /dt_100A/	-	46	-	ns
Q _{rr}	Reverse Recovery Charge	l _{SD} =60A, dl _{SD} /dt=100A/μs	-	98	-	nC

^{**} Drain current is limited by junction temperature

^{***} VD=100V



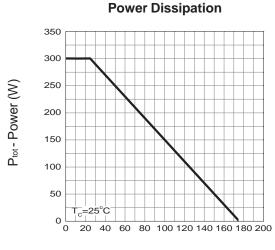
Electrical Characteristics (Cont.) $(T_c = 25^{\circ}C \text{ Unless Otherwise Noted})$

Symbol	Parameter	Test Conditions	HY3215			Unit	
Symbol	Parameter	rest Conditions	Min.	Тур.	Max.	Offic	
Dynamic (Dynamic Characteristics						
R_G	Gate Resistance	V_{GS} =0V, V_{DS} =0V, F =1MHz	-	3.2	-	Ω	
C _{iss}	Input Capacitance	$V_{GS}=0V$,	-	5785	-		
C _{oss}	Output Capacitance	V _{DS} =25V,	-	548	-	pF	
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz	-	321	-		
t _{d(ON)}	Turn-on Delay Time	V_{DD} =75V, R _G = 3 Ω , I_{DS} =60A, V_{GS} =10V,	-	26	-		
Tr	Turn-on Rise Time		-	39	-	ns	
t _{d(OFF)}	Turn-off Delay Time		-	77	-	115	
T_f	Turn-off Fall Time		-	58	ı		
Gate Charge Characteristics							
Q_g	Total Gate Charge	V _{DS} =120 V, V _{GS} =10V,	-	137	-		
Q_gs	Gate-Source Charge		-	28	-	nC	
Q_gd	Gate-Drain Charge	7.03	-	46	-		

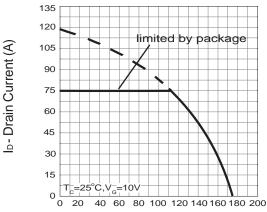
Note * : Pulse test ; pulse width $\leq\!300\mu s,$ duty cycle $\leq\!2\%.$



Typical Operating Characteristics



135

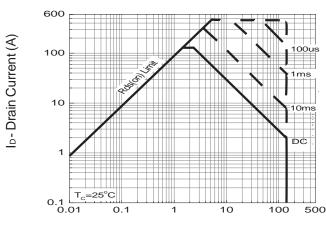


Drain Current

T_c- Case Temperature (°C)

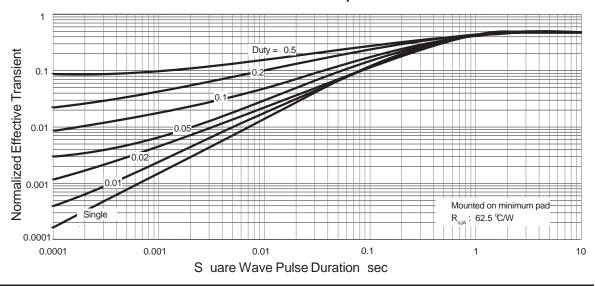
T_c-Case Temperature (°C)

Safe Operation Area



V_{DS} - Drain - Source Voltage (V)

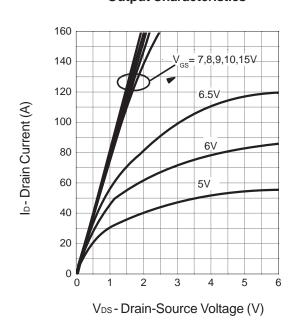
Thermal Transient Impedance



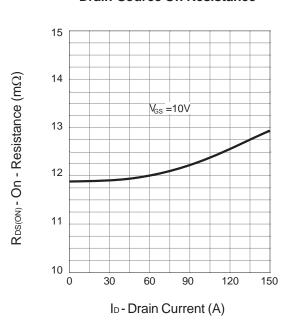


Typical Operating Characteristics (Cont.)

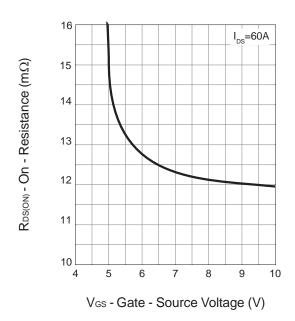
Output Characteristics



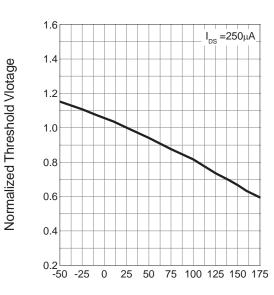
Drain-Source On Resistance



Drain-Source On Resistance



Gate Threshold Voltage

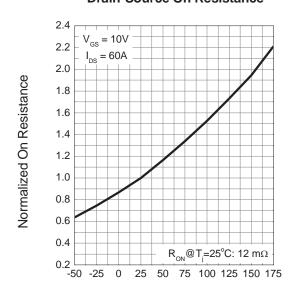


T_j - Junction Temperature (°C)



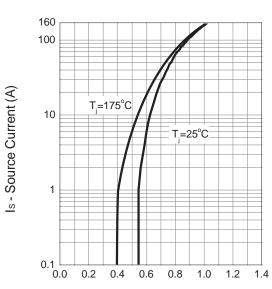
Typical Operating Characteristics (Cont.)

Drain-Source On Resistance



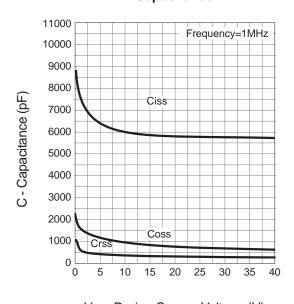
T_j- Junction Temperature (°C)

Source-Drain Diode Forward



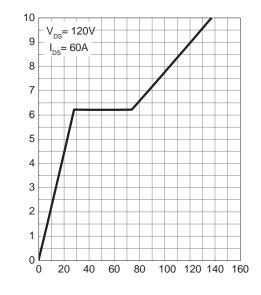
VsD - Source-Drain Voltage (V)

Capacitance



V_{DS} - Drain - Source Voltage (V)

Gate Charge

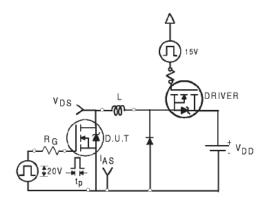


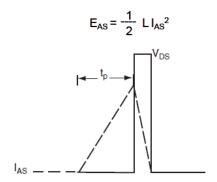
Q_G - Gate Charge (nC)

Ves - Gate-source Voltage (V)

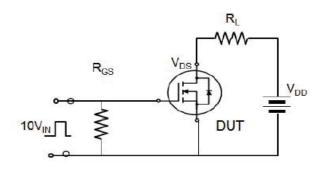


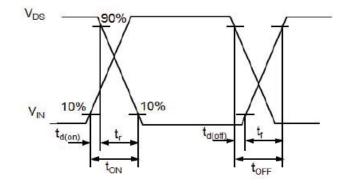
Avalanche Test Circuit



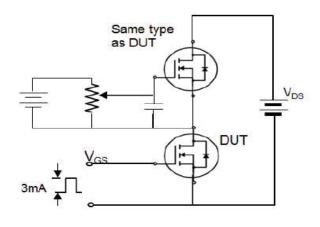


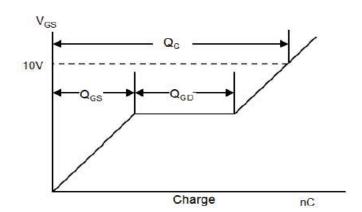
Switching Time Test Circuit





Gate Charge Test Circuit



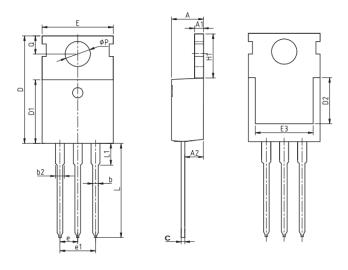




Package Type	Unit	Quantity
TO-220FB-3L	Tube	50

Package Information

TO-220FB-3L



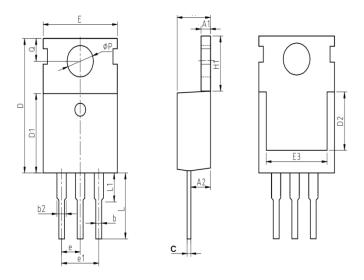
SYMBOL	mm				
STIVIBOL	MIN	NOM	MAX		
А	4.37	4.57	4.77		
A1	1.25	1.30	1.45		
A2	2.20	2.40	2.60		
b	0.70	0.80	0.95		
b2	1.17	1.27	1.47		
С	0.40	0.50	0.65		
D	15.10	15.60	16.10		
D1	8.80	9.10	9.40		
D2	5.50	-	-		
E	9.70	10.00	10.30		
E3	7.00	-	-		
е		2.54 BSC			
e1		5.08 BSC			
H1	6.25	6.50	6.85		
L	12.75	13.50	13.80		
L1	-	3.10	3.40		
ФР	3.40	3.60	3.80		
Q	2.60	2.80	3.00		



Package Type	Unit	Quantity
TO-220FB-3S	Tube	50

Package Information

TO-220FB-3S



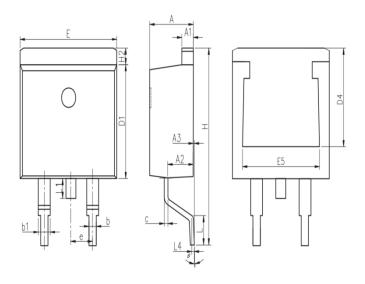
CVMDOL	mm			
SYMBOL	MIN	NOM	MAX	
А	4.37	4.57	4.77	
A1	1.25	1.30	1.45	
A2	2.20	2.40	2.60	
b	0.70	0.80	0.95	
b2	1.17	1.27	1.47	
С	0.40	0.50	0.65	
D	15.10	15.60	16.10	
D1	8.10	9.10	9.40	
D2	5.50	-	-	
E	9.70	10.00	10.30	
E3	7.00	-	-	
е		2.54 BSC		
e1		5.08 BSC		
H1	6.25	6.50	6.85	
L	6.80	7.00	7.20	
L1	-	3.10	3.40	
ФР	3.40	3.60	3.80	
Q	2.60	2.80	3.00	



Package Type	Unit	Quantity
TO-263-2L	Reel	50

Package Information

TO-263-2L



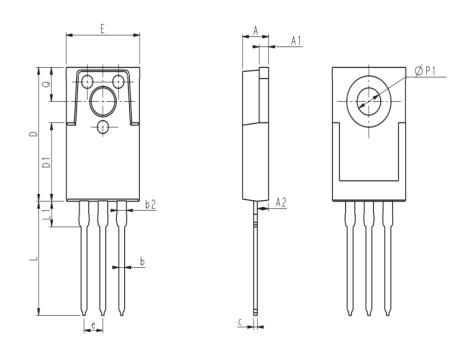
CVMDOL	mm			
SYMBOL	MIN	NOM	MAX	
А	4.37	4.57	4.77	
A1	1.22	1.27	1.42	
A2	2.49	2.69	2.89	
A3	0	0.13	0.25	
b	0.7	0.81	0.96	
b1	1.17	1.27	1.47	
С	0.3	0.38	0.53	
D1	8.5	8.7	8.9	
D4	6.6	-	-	
E	9.86	10.16	10.36	
E5	7.06	-	-	
е		2.54 BSC	;	
Н	14.7	15.1	15.5	
H2	1.07	1.27	1.47	
L	2	2.3	2.6	
L1	1.4	1.55	1.7	
L4	0.25 BSC			
θ	0°	5°	9°	



Package Type	Unit	Quantity
TO-3PS-3L	Tube	50

Package Information

TO-3PS-3L



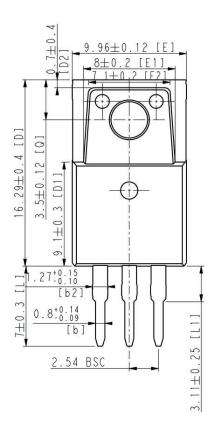
SYMBOL		mm	
STIVIBUL	MIN	NOM	MAX
А	3.36	3.56	3.76
A1	1.25	1.30	1.40
A2	1.39	1.54	1.69
b	0.75	0.80	0.90
b2	1.17	1.27	1.42
С	0.45	0.50	0.60
D	15.45	15.70	15.95
D1	9.00	9.20	9.40
E	9.88	10.00	10.20
е	2	.54 BS	С
L	13.20	13.40	13.60
L1	-	3.00	3.30
ФР1	3.20 REF		
Q	3.88	4.00	4.12

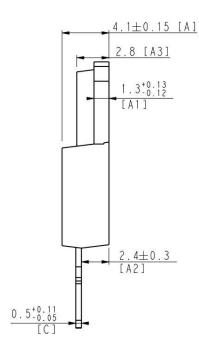


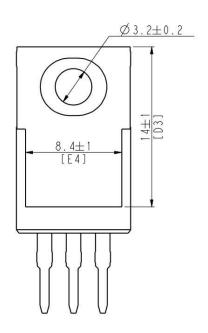
Package Type	Unit	Quantity
TO-3PM-3S	Tube	50

Package Information

TO-3PM-3S

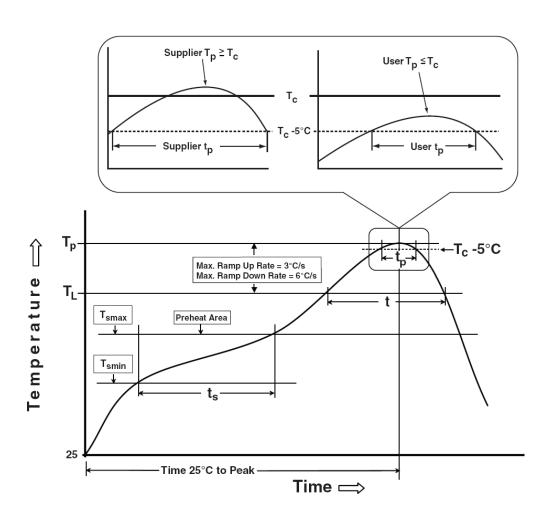








Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly		
$\begin{array}{c} \textbf{Preheat \& Soak} \\ \textbf{Temperature min } (\textbf{T}_{smin}) \\ \textbf{Temperature max } (\textbf{T}_{smax}) \\ \textbf{Time } (\textbf{T}_{smin} \text{ to } \textbf{T}_{smax}) \ (\textbf{t}_{s}) \end{array}$	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds		
Average ramp-up rate (T _{smax} to T _P)	3 °C/second max.	3°C/second max.		
Liquidous temperature (T _L) Time at liquidous (t _L)	183 °C 60-150 seconds	217 °C 60-150 seconds		
Peak package body Temperature $(T_p)^*$	See Classification Temp in table 1	See Classification Temp in table 2		
Time $(t_P)^{**}$ within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds		
Average ramp-down rate (T _p to T _{smax})	6 °C/second max.	6 °C/second max.		
Time 25°C to peak temperature	6 minutes max.	8 minutes max.		
* Tolerance for peak profile Temperature (Tp) is defined as a supplier minimum and a user maximum.				

^{**} Tolerance for time at peak profile temperature (tp) is defined as a supplier minimum and a user maximum.

HY3215P/M/B/PS/PM



Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm ³ <350	Volume mm³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package	Volume mm ³	Volume mm ³	Volume mm ³
Thickness	<350	350-2000	>2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	168Hrs/500Hrs/1000Hrs,Bias@125°C
PCT	JESD-22, A102	96 Hrs, 100% RH, 2atm, 121°C
ТСТ	JESD-22, A104	500 Cycles, -55°C~150°C

Customer Service

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